NSN 5961-00-233-4851

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-233-4851 **Inclosure Material:** Metal **Overall Length:** Between 0.240 inches and 0.260 inches **Terminal Length:** Between 1.500 inches and 1.750 inches **Overall Diameter:** Between 0.335 inches and 0.370 inches **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method: Terminal Terminal Circle Diameter:** 0.200 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 2.2 forward voltage, peak and 1.0 gate trigger voltage, dc and 50.0 reverse voltage, peak **Current Rating Per Characteristic:** 350.00 microamperes forward current, total rms preset and 220.00 milliamperes forward current, total rms megahertz **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Internal junction configuration arrangement pnpn **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 3 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/276 government specification Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

No

Demilitarization: